

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	790	\$4silicon and (("FET" or transistor) and (channel adj (zone or region or area))) and (web or slot) and source and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:15
L2	268	1 and (epi or epitaxial\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:16
L3	119	2 and body	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:17
L4	81	3 and (@ad<"20020731" or @rlad<"20020731")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:18
L5	5	4 and pillar	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:20
L6	14	(US-20030067034-\$ or US-20040065909-\$ or US-20050029568-\$).did. or (US-5136349-\$ or US-5753942-\$ or US-6274904-\$ or US-6479352-\$ or US-6576516-\$ or US-6683344-\$ or US-6794251-\$ or US-6825514-\$ or US-6894329-\$ or US-6900109-\$).did. or (GB-2319395-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2005/11/18 15:20
L7	76	4 not (5 6)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:27
L8	0	((epitaxial or epi) and \$4silicon and gate and (channel adj (zone or area or region or well)) and concentrant\$4).clm.	US-PGPUB	OR	ON	2005/11/18 15:29
L9	55	((epitaxial or epi) and \$4silicon and gate and (channel adj (zone or area or region or well)) and concentrat\$4).clm.	US-PGPUB	OR	ON	2005/11/18 15:29
L10	1	9 and (web\$3 or slot\$3)	US-PGPUB	OR	ON	2005/11/18 15:29
L11	55	9 not 7	US-PGPUB	OR	ON	2005/11/18 15:29
L12	199	257/285.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:36
L13	756	257/329.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/18 15:37
S9	6	"2319395"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:37
S10	10	"5736445"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:46

S11	3	"5879968"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 11:38
S12	9	("4879254"   "4898835"   "4987098"   "5023191"   "5072266"   "5164327"   "5298442"   "5453390"   "5486715").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 11:38
S13	101	weber-hans.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:46
S14	0	ahler5s-dirk.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:46
S15	34	ahlers-dirk.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S16	11	wahl-uwe.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S17	303	tihanyi-jeno.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S18	2	tihanyl-jeno.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S19	39	willmeroth-armin.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S20	445	S13 S15 S16 S17 S18 S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:47
S21	3	S20 and ("FET" or (field adj2 effect adj2 transistor) or (field-effect adj transistor)) and polysilicon and channel and source and gate and pillar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:50
S22	22	S20 and ("FET" or (field adj2 effect adj2 transistor) or (field-effect adj transistor)) and polysilicon and channel and source and gate and (hole or pillar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:52

S24	52	("20010050549"   "20010053568"   "3171068"   "3841917"   "3925803"   "3961356"   "4003072"   "4055884"   "4072975"   "4101922"   "4145700"   "4320410"   "4345265"   "4366495"   "4376286"   "4404575"   "4417385"   "4561003"   "4593302"   "4748103"   "4754310"   "4775881"   "4777149"   "4895810"   "4914058"   "4926226"   "4941026"   "4974059"   "4975782"   "4994871"   "5008725"   "5010025"   "5019522"   "5045903"   "5072269"   "5089434"   "5126807"   "5182234"   "5216275"   "5231474"   "5283201"   "5430315"   "5438215"   "5473180"   "5559353"   "5648283"   "5747831"   "5801417"   "5883411"   "5973360"   "6037631").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 12:19
S25	632	257/302.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:21
S26	56	S25 and source and gate and pillar and epitaxi\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:22
S27	55	S26 not (S20 S21 S22 S11)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:22
S28	42	S27 and (channel and polysilicon and (hole or opening or trench))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:23
S29	7	S28 and ((impurity or dop\$4) near2 concentrati\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:25
S30	27	(S28 not S29) and (deplet\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:27
S31	10	coolMOS and epitaxi\$3 and well	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 12:27
S32	3	("4370180"   "5164325"   "6037631").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 12:33
S33	11	("6274904").URPN.	USPAT	OR	ON	2005/08/02 12:34
S34	19	("20010026977"   "20010036704"   "20010053568"   "4140558"   "4419150"   "4569701"   "4711017"   "4893160"   "5108783"   "5216275"   "5675173"   "6188104"   "6215149"   "6274904"   "6455379"   "6472678"   "6472708"   "6479352"   "6495884").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 15:44
S35	1	("6576516").URPN.	USPAT	OR	ON	2005/08/02 15:46
S36	20	("20010026977"   "20010036704"   "20010041400"   "20010046739"   "20010053568"   "20020008258"   "20020123195"   "20020132405"   "20020135014"   "4140558"   "4419150"   "4569701"   "4711017"   "4893160"   "4914058"   "5108783"   "5216275"   "6376878"   "6475864"   "6576516").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 15:47
S37	6	(vertical near2 deplet\$4 near3 ("FET" or "MOSFET" or (field adj effect adj transistor))) and (gate and source and channel and polysilicon and well and epitaxi\$3) and (slot\$3 or bar\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:21

S38	8	(vertical near2 deplet\$4 near3 ("FET" or "MOSFET" or (field adj effect adj transistor))) and (gate and source and channel and polysilicon and well and epitaxi\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:44
S39	2	S38 not S37	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:22
S40	230583	"257"/("302", "304").ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:23
S41	4	S40 and (vertical near2 deplet\$4 near3 ("FET" or "MOSFET" or (field adj effect adj transistor)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:46
S42	6	("438"/("135", "268").ccls.) and (vertical near2 deplet\$4 near3 ("FET" or "MOSFET" or (field adj effect adj transistor)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:48
S43	2902	(S40 not S41) and (vertical\$3 near5 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:49
S44	1321	S43 and (gate with (hole or trench or opening or pillar))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:50
S45	550	S44 and (source and gate and channel and polysilicon and epitaxi\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:50
S46	4	S45 and (coolMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 17:54
S47	336	(epitaxial\$3 and (web or slot) and well and polysilicon and (hole or opening or trench) and transistor and source and channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:25
S55	81	S47 and (vertical with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:25
S56	81	S55 and (impurity or dop\$4 or implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:26
S57	50	S56 and ("MOS" or "PMOS" or "NMOS")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:28
S58	50	S57 and (epitaxia\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:29

S59	34	S58 and concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:29
S60	4	S59 and (pillar)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:32
S61	30	S59 not (S34 S35 S37 S38 S39 S41 S42 S46 S60)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/02 19:32
S62	20	("20010026977"   "20010036704"   "20010053568"   "4140558"   "4419150"   "4569701"   "4711017"   "4893160"   "5108783"   "5216275"   "5675173"   "6188104"   "6215149"   "6274904"   "6455379"   "6465304"   "6472678"   "6472708"   "6479352"   "6495884").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 20:02
S63	0	("6794251").URPN.	USPAT	OR	ON	2005/08/02 20:05
S64	3	"6576516"	USPAT	OR	ON	2005/08/02 20:05
S65	146	(reduc\$4 near3 (well adj (area or region or zone))) and ("MOSFET" or "FET" or (field adj effect adj transistor)) and gate and polysilicon and (mask or photoresist or resist)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:16
S66	36	S65 and (polysilicon with (hole or trench or opening or slot or web))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:16
S67	34	S66 and ("MOSFET" or "FET" or (field adj effect adj transistor) with vertical\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:16
S68	34	S67 and gate and source	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:17
S69	30	("4587713"   "4835586"   "4980740"   "5034336"   "5057884"   "5089864"   "5095343"   "5136349"   "5160985"   "5168331"   "5170239"   "5171705"   "5198687"   "5245202"   "5304821"   "5323036"   "5326993"   "5338961"   "5349212"   "5396087"   "5397905"   "5468668"   "5471075"   "5485023"   "5488236"   "5548133"   "5668026"   "5702961"   "5742076"   "5753942"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/03 11:23
S70	2	S66 not S67	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:32
S71	110	S65 not S66	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:32
S72	55	S71 and (dual or multiple)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:34
S73	0	S71 and ((dual or multiple) with polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/03 11:33